

N-Channel Super-junction MOSFET Gen III

MOSFET

Metal Oxide Semiconductor Field Effect Transistor

650V Super-junction Gen III

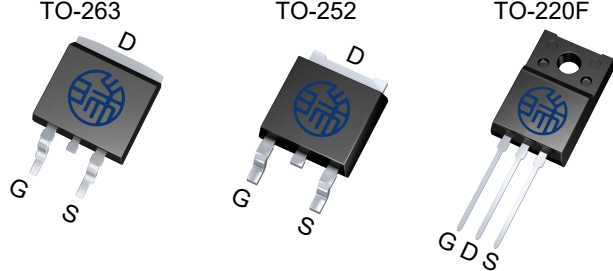
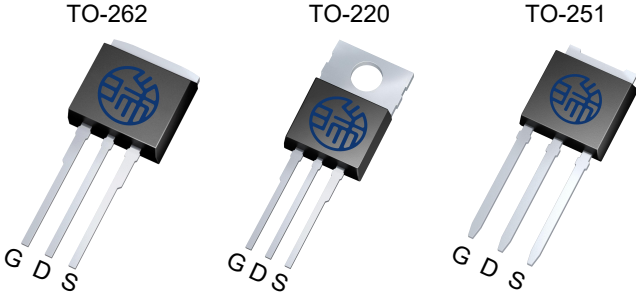
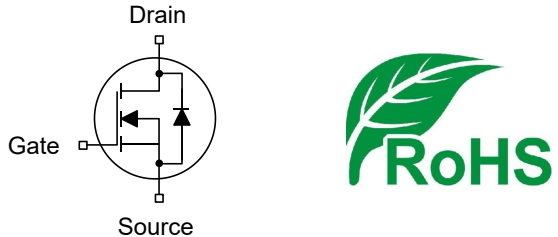
650V Super-junction Gen III Power Transistor

HRD65T540x Data Sheet

Rev. 2020 V1.0



650V Super-junction Power MOSFET Gen III

<p>Description</p> <p>650V Super-junction MOSFET Gen III</p> <p>Super-junction MOSFET Gen III is designed by HR-Micro Semiconductor Company, according to the SJ principle. This device provides an excellent Gate charge and $R_{DS(on)}$, which leads to extremely low communication and conduction losses. So it is very suitable for AC/DC power conversion, Laptop adapter, Lighting, and industrial power applications.</p>			
<p>Features</p> <ul style="list-style-type: none"> • Very low FOM $R_{DS(on)} \times Q_g$ • 100% avalanche tested • Easy to use/drive • RoHS compliant 			
<p>Applications</p> <ul style="list-style-type: none"> • Switch Mode Power Supply (SMPS) • Uninterruptible Power Supply (UPS) • Power Factor Correction (PFC) • Charger 			
<p>Key Performance Parameters</p>			
<p>Parameter</p>	<p>Value</p>	<p>Unit</p>	
<p>$V_{DS} @ T_{J,max}$</p>	<p>700</p>	<p>V</p>	
<p>$R_{DS(on),max}$</p>	<p>0.54</p>	<p>Ω</p>	
<p>$Q_{g,typ}$</p>	<p>14.2</p>	<p>nC</p>	
<p>I_D</p>	<p>7</p>	<p>A</p>	
<p>$I_{D,pulse}$</p>	<p>21</p>	<p>A</p>	
<p>$E_{OSS} @ 400V$</p>	<p>1.48</p>	<p>μJ</p>	
<p>Body Diode di_f/dt</p>	<p>500</p>	<p>A/μs</p>	
<p>Device Marking and Package Information</p>			
<p>Device</p>	<p>Package</p>	<p>Marking</p>	
<p>HRD65T540B</p>	<p>TO-263</p>	<p>D65T540B</p>	
<p>HRD65T540D</p>	<p>TO-252</p>	<p>D65T540D</p>	
<p>HRD65T540F</p>	<p>TO-220F</p>	<p>D65T540F</p>	
<p>HRD65T540L</p>	<p>TO-262</p>	<p>D65T540L</p>	
<p>HRD65T540P</p>	<p>TO-220</p>	<p>D65T540P</p>	
<p>HRD65T540U</p>	<p>TO-251</p>	<p>D65T540U</p>	

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted			
Parameter	Symbol	Value	Unit
Drain-Source Voltage($V_{GS}=0\text{V}$)	V_{DS}	650	V
Continuous Drain Current ¹⁾	I_D	$T_C = 25^\circ\text{C}$	7
		$T_C = 100^\circ\text{C}$	4.2
Pulsed Drain Current ²⁾	$I_{D,pulse}$	21	A
Gate-Source Voltage	V_{GS}	± 30	V
Single Pulse Avalanche Energy	E_{AS}	156	mJ
Repetitive Avalanche Energy	E_{AR}	0.3	mJ
Avalanche Current	I_{AR}	1.7	A
MOSFET dv/dt Ruggedness, $V_{DS} = 0 \dots 480\text{V}$	dv/dt	50	V/ns
Power Dissipation For TO-263、TO-252、TO-262、TO-220、TO-251	P_D	50	W
Power Dissipation For TO-220F		25	
Continuous Diode Forward Current	I_S	6.0	A
Diode Pulsed Current ²⁾	$I_{S,pulse}$	21	
Reverse Diode dv/dt ³⁾	dv/dt	15	V/ns
Maximum Diode Commutation Speed	di _F /dt	500	A/ μs
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	$^\circ\text{C}$

Thermal Resistance For TO-263、TO-252、TO-262、TO-220、TO-251			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	2.5	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62	

Thermal Resistance For TO-220F			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	5	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	80	

Notes

- 1) Limited by maximum junction temperature.
- 2) Repetitive Rating: Pulse width limited by maximum junction temperature.
- 3) Identical low side and high side switch with identical R_G .

Electrical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	650	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 650V$ $V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	μA
		$V_{DS} = 650V$ $V_{GS} = 0V, T_J = 150^\circ\text{C}$	--	--	100	
Gate-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 30V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	3.0	3.5	4.0	V
Drain-Source On-State-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 3.5A$	--	0.475	0.54	Ω
Gate Resistance	R_G	$f = 1.0\text{MHz}$ open drain	--	3.9	--	Ω
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 100V$ $f = 1.0\text{MHz}$	--	439	--	μF
Output Capacitance	C_{oss}		--	20	--	
Reverse Transfer Capacitance	C_{rss}		--	0.7	--	
Total Gate Charge	Q_g	$V_{DD} = 520V, I_D = 7A$ $V_{GS} = 10V$	--	14.2	--	nC
Gate-Source Charge	Q_{gs}		--	4.6	--	
Gate-Drain Charge	Q_{gd}		--	5.0	--	
Gate Plateau Voltage	$V_{Plateau}$		--	5.7	--	V
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 400V, I_D = 7A$ $R_G = 15\Omega, V_{GS} = 10V$	--	8	--	ns
Turn-on Rise Time	t_r		--	6	--	
Turn-off Delay Time	$t_{d(off)}$		--	59	--	
Turn-off Fall Time	t_f		--	10	--	
Drain-Source Body Diode Characteristics						
Body Diode Forward Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{SD} = 3.5A$ $V_{GS} = 0V$	--	0.9	1.2	V
Reverse Recovery Time	t_{rr}	$V_R = 400V$ $I_F = 3.5A, di_F/dt = 100A/\mu s$	--	185	--	ns
Reverse Recovery Charge	Q_{rr}		--	0.85	--	μC
Peak Reverse Recovery Current	I_{rrm}		--	9	--	A

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

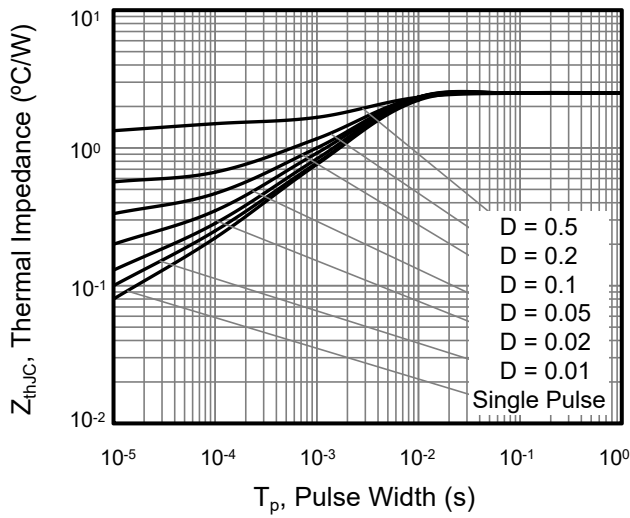


Figure 1. Transient Thermal Impedance For TO-263/TO-252/TO-262/TO-220/TO-251

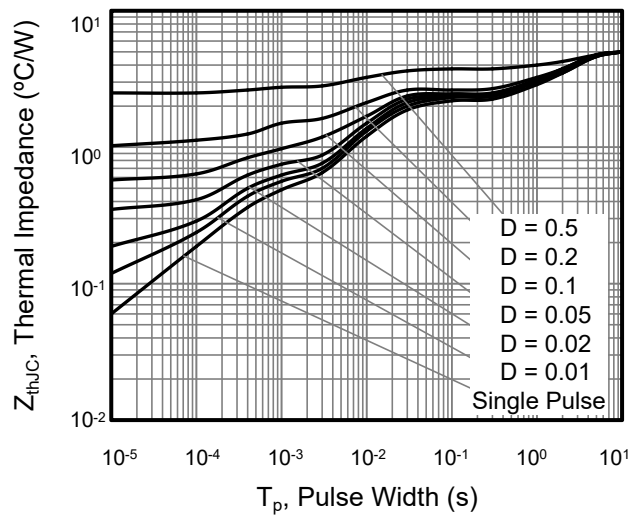


Figure 2. Transient Thermal Impedance For TO-220F

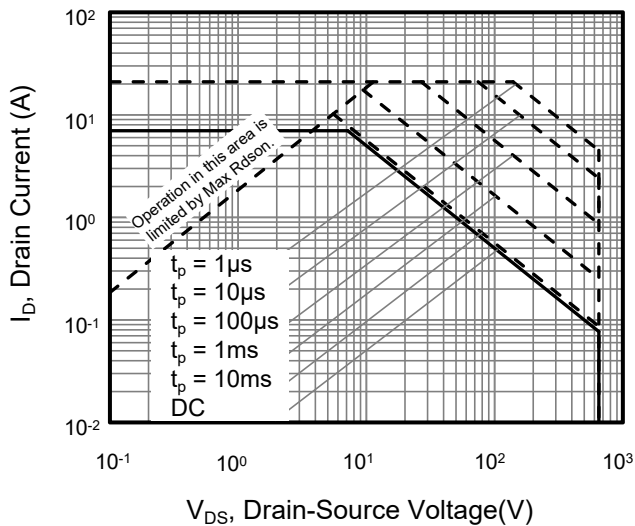


Figure 3. Safe Operation Area For TO-263/TO-252/TO-262/TO-220/TO-251

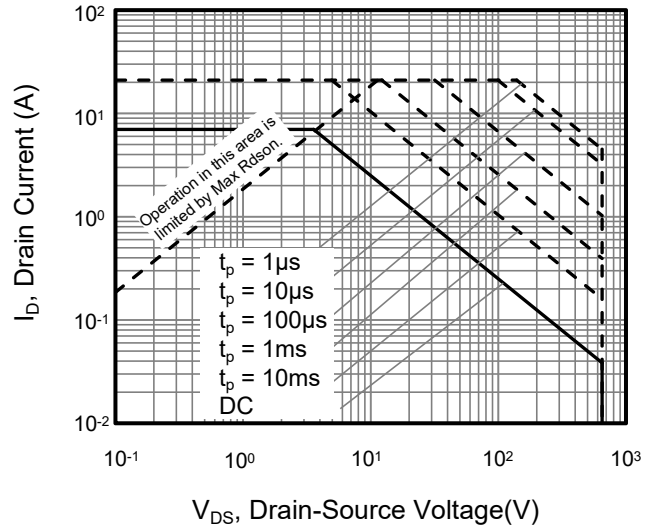


Figure 4. Safe Operation Area For TO-220F

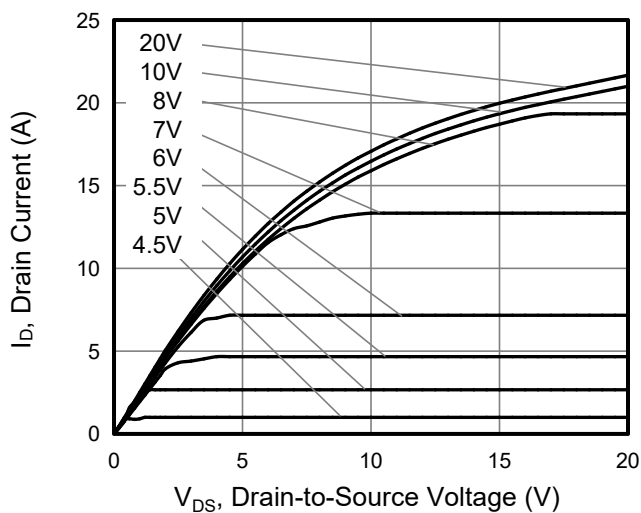


Figure 5. Output Characteristics

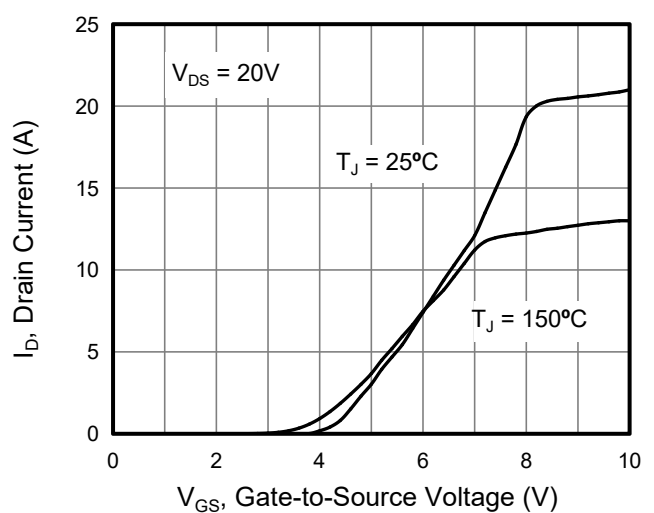


Figure 6. Transfer Characteristics

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

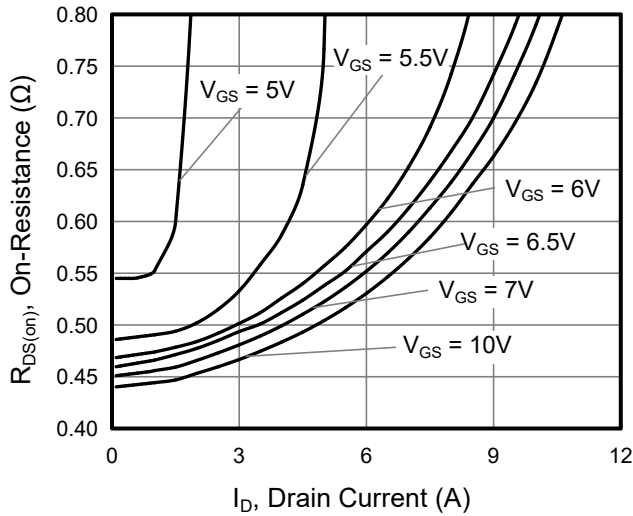


Figure 7. On-Resistance vs Drain Current

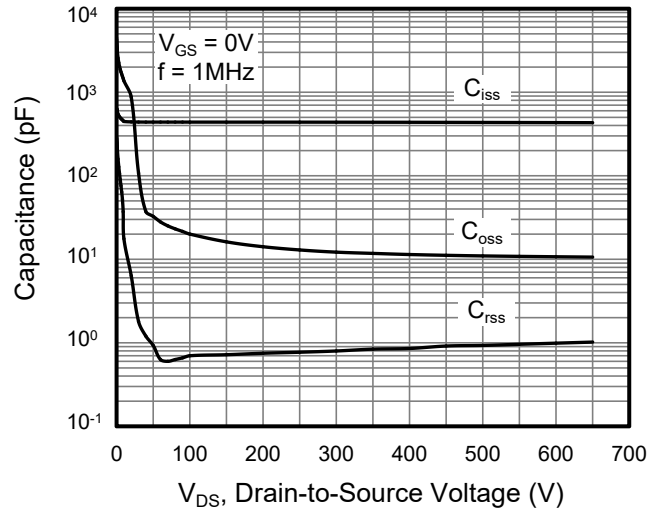


Figure 8. Capacitance

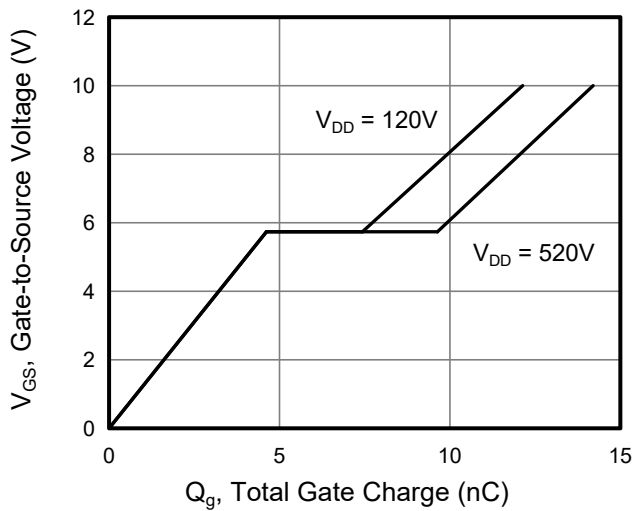


Figure 9. Gate Charge

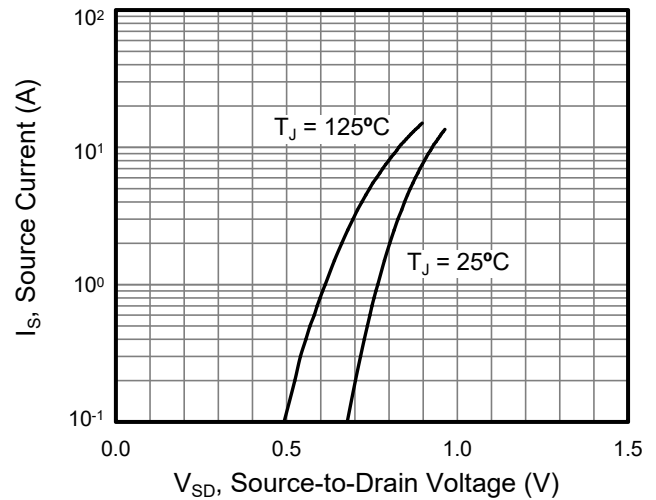


Figure 10. Body Diode Forward Voltage

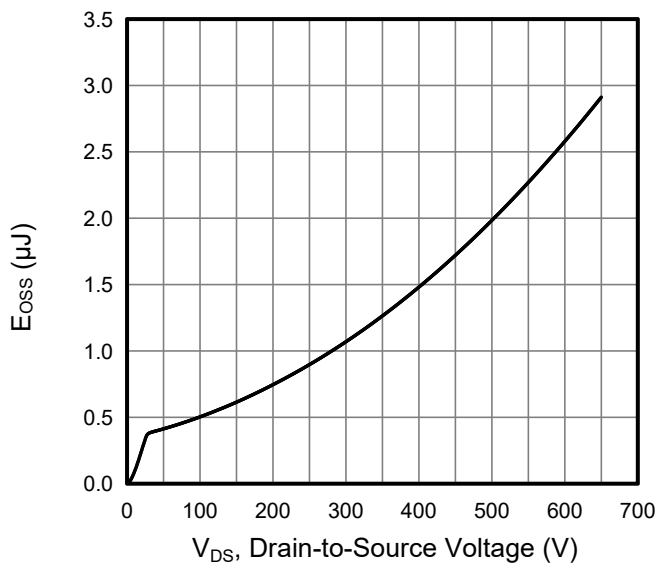


Figure 11. Typ. Coss Stored Energy

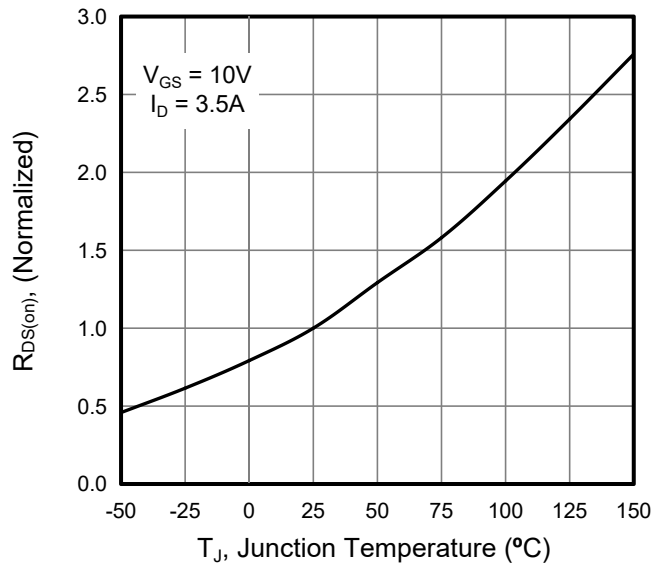


Figure 12. On-Resistance vs Temperature

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

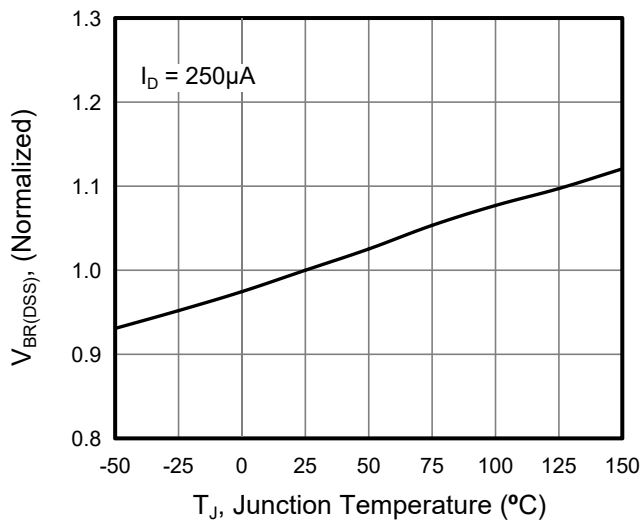


Figure 13. Breakdown Voltage vs Junction Temperature

Figure A: Gate Charge Test Circuit and Waveform

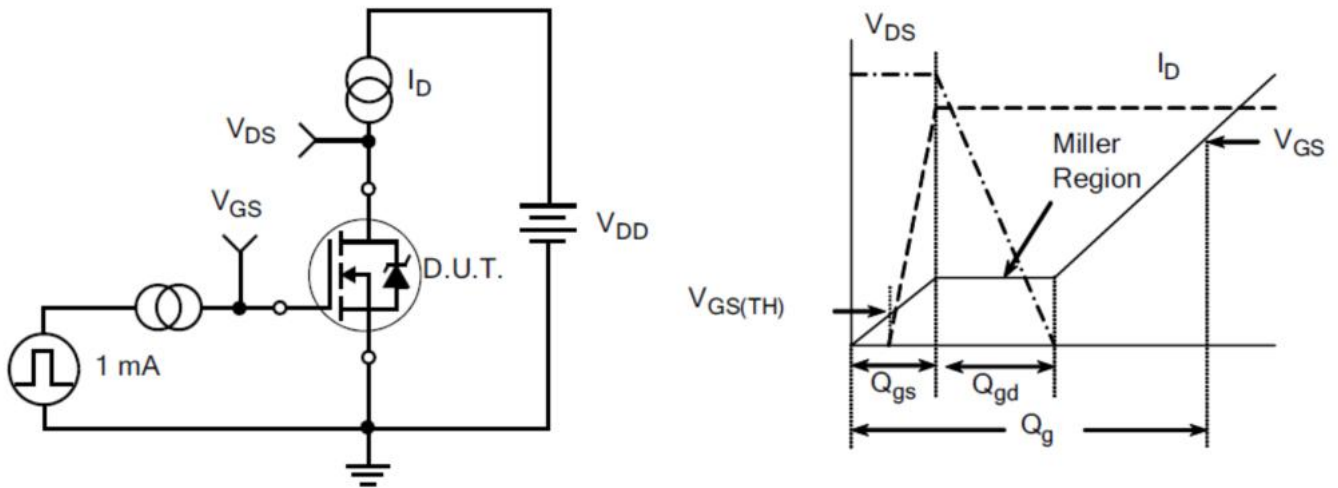


Figure B: Resistive Switching Test Circuit and Waveform

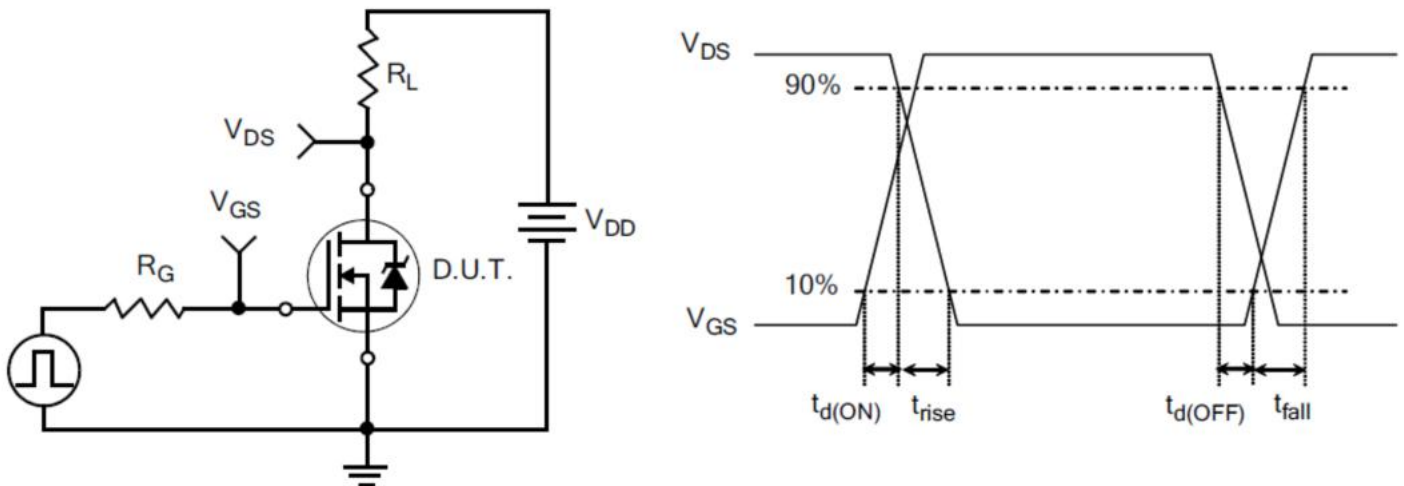
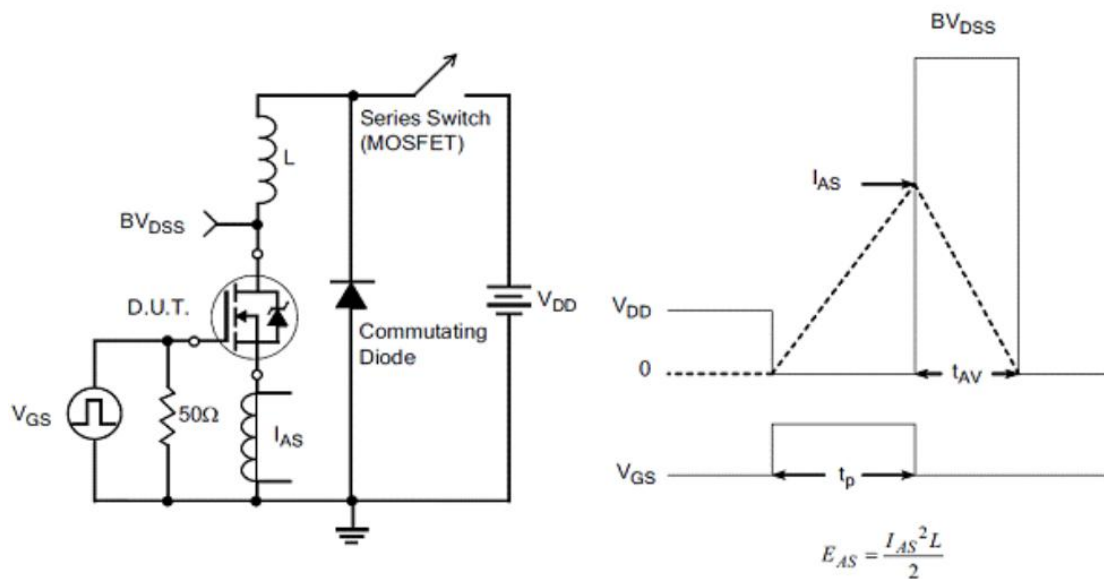
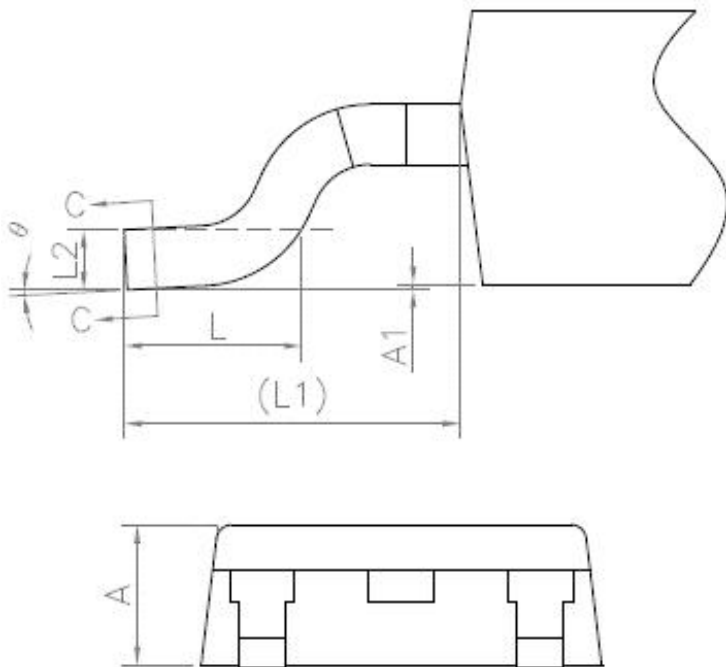
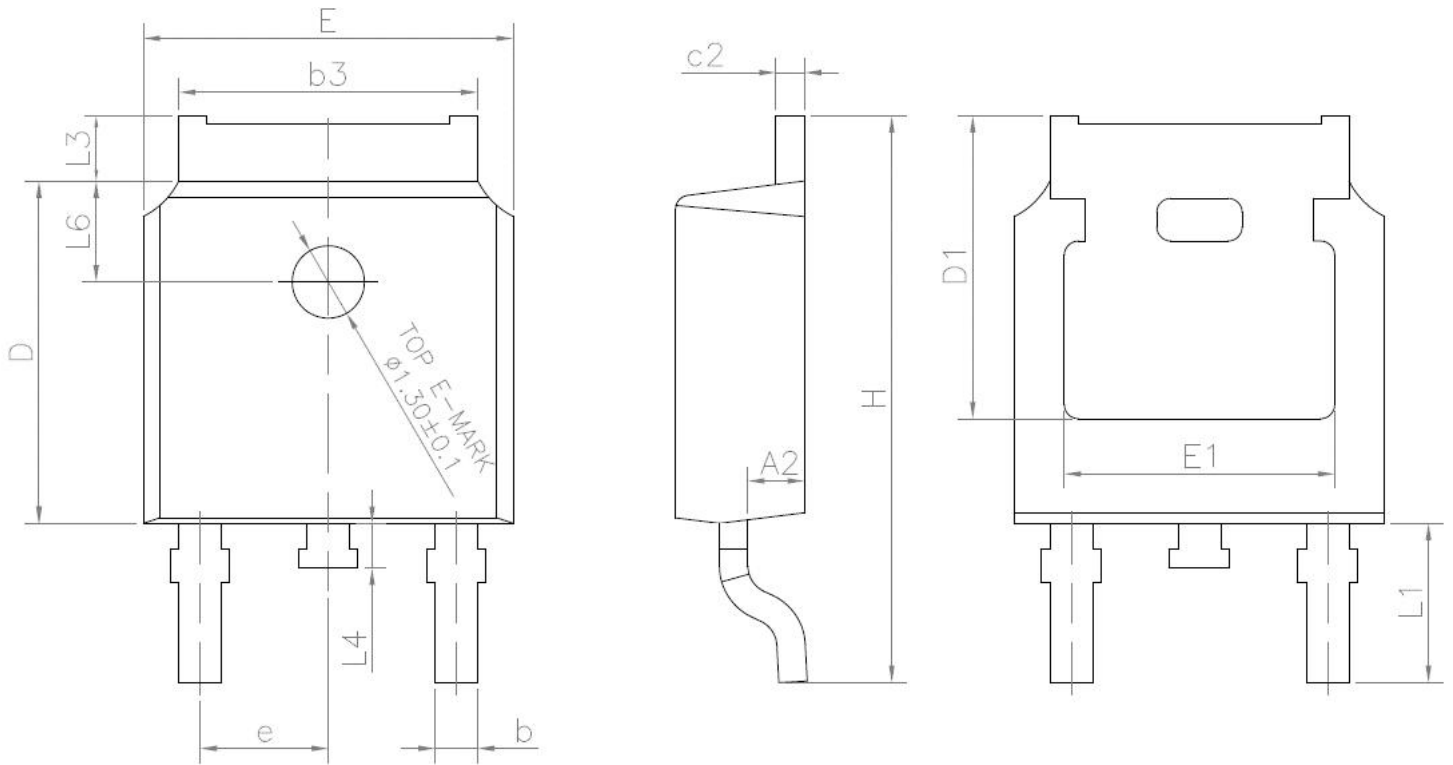


Figure C: Unclamped Inductive Switching Test Circuit and Waveform

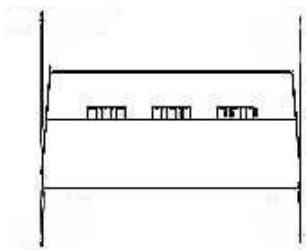
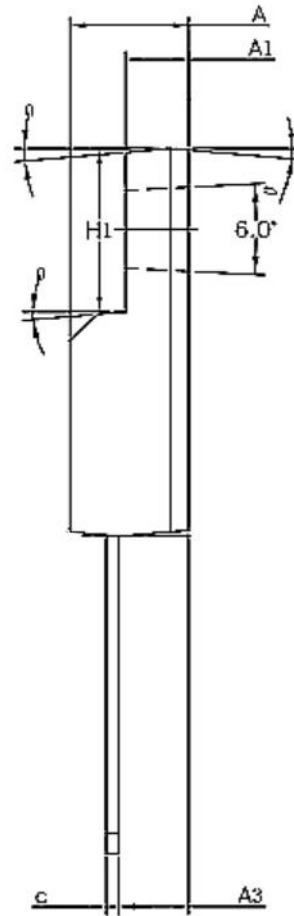
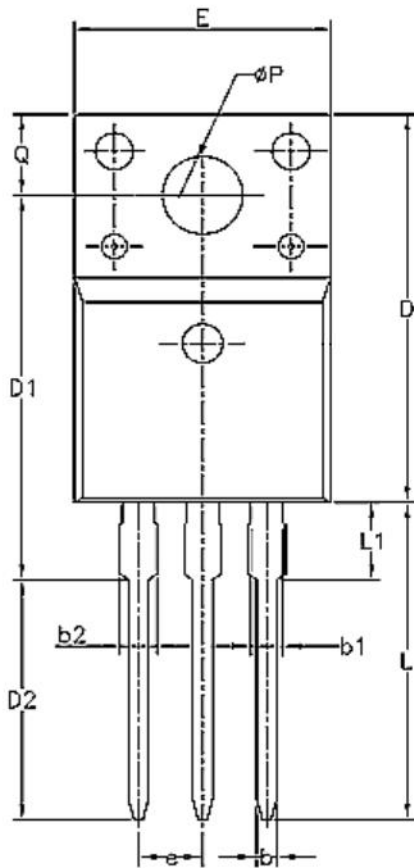


Outlines TO-252 Package



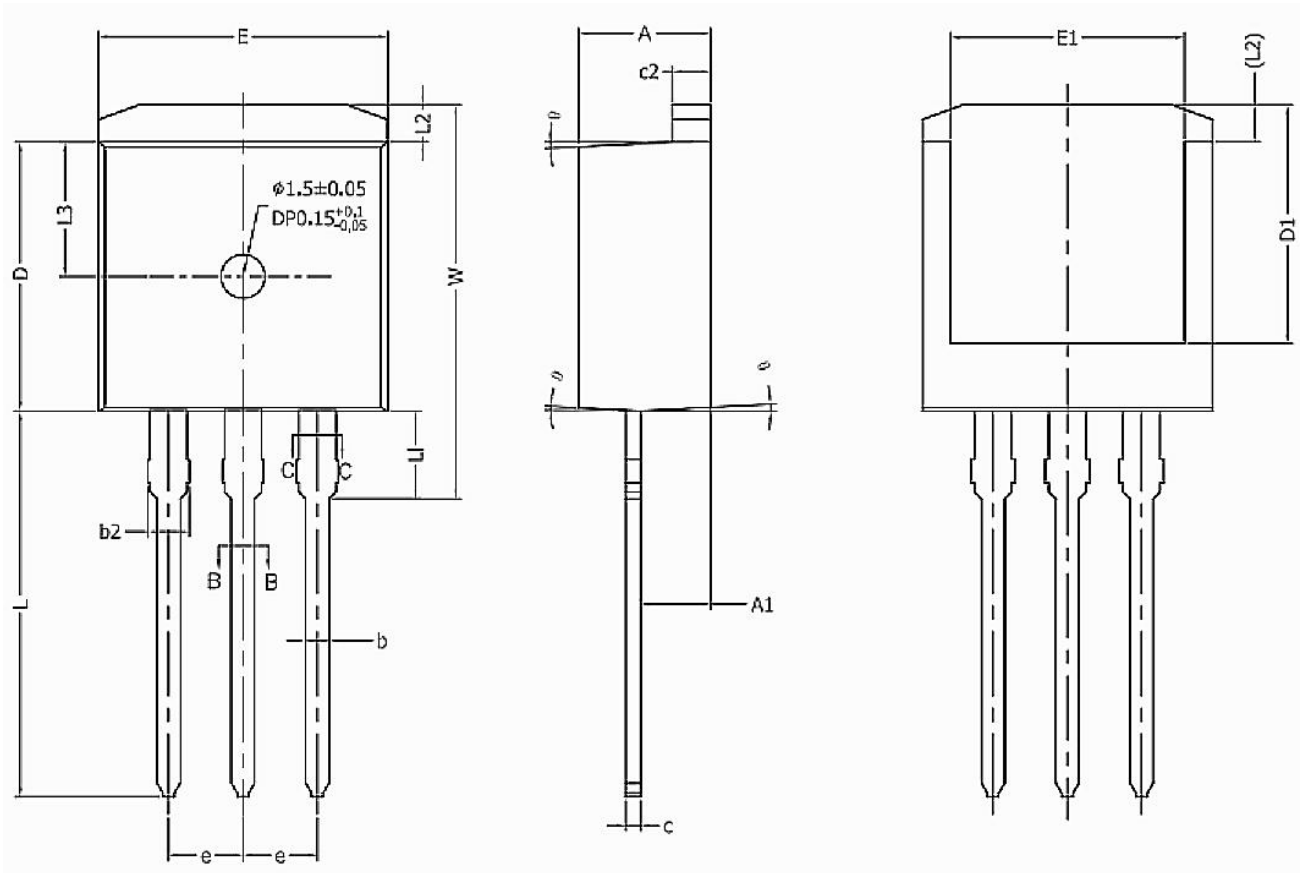
SYMBOL	MIN	NOM	MAX
A	2.2	2.3	2.4
A1	0	--	0.2
A2	0.9	1.035	1.17
b	0.645	--	0.9
b3	5.13	5.326	5.46
c	0.43	--	0.61
c2	0.41	--	0.61
D	5.98	6.1	6.22
D1	5.244	--	--
E	6.4	6.6	6.73
E1	4.63	--	--
e	2.186	2.286	2.386
H	9.4	10.04	10.5
L	1.38	1.5	1.75
L1	2.6	2.872	3
L2	0.5	0.509	0.52
L3	0.88	--	1.28
L4	0.5	--	1
L6	1.5	1.7	1.95
θ	0°	--	10°

Outlines TO-220F Package



SYMBOL	MIN	NOM	MAX
A	4.5	4.7	4.9
A1	2.34	2.54	2.74
A3	2.56	2.76	2.96
b	0.7	---	0.95
b1	1.18	---	1.43
b2	---	---	1.55
c	0.4	0.5	0.65
D	15.57	15.87	16.17
D1	15.35	15.675	15.95
D2	9.6	9.875	10.15
E	9.96	10.16	10.36
e	2.54 BSC		
H1	6.48	6.68	6.88
L	12.68	12.98	13.28
L1	---	---	3.5

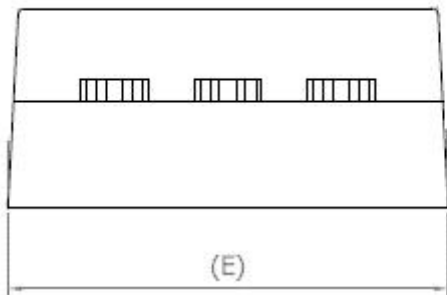
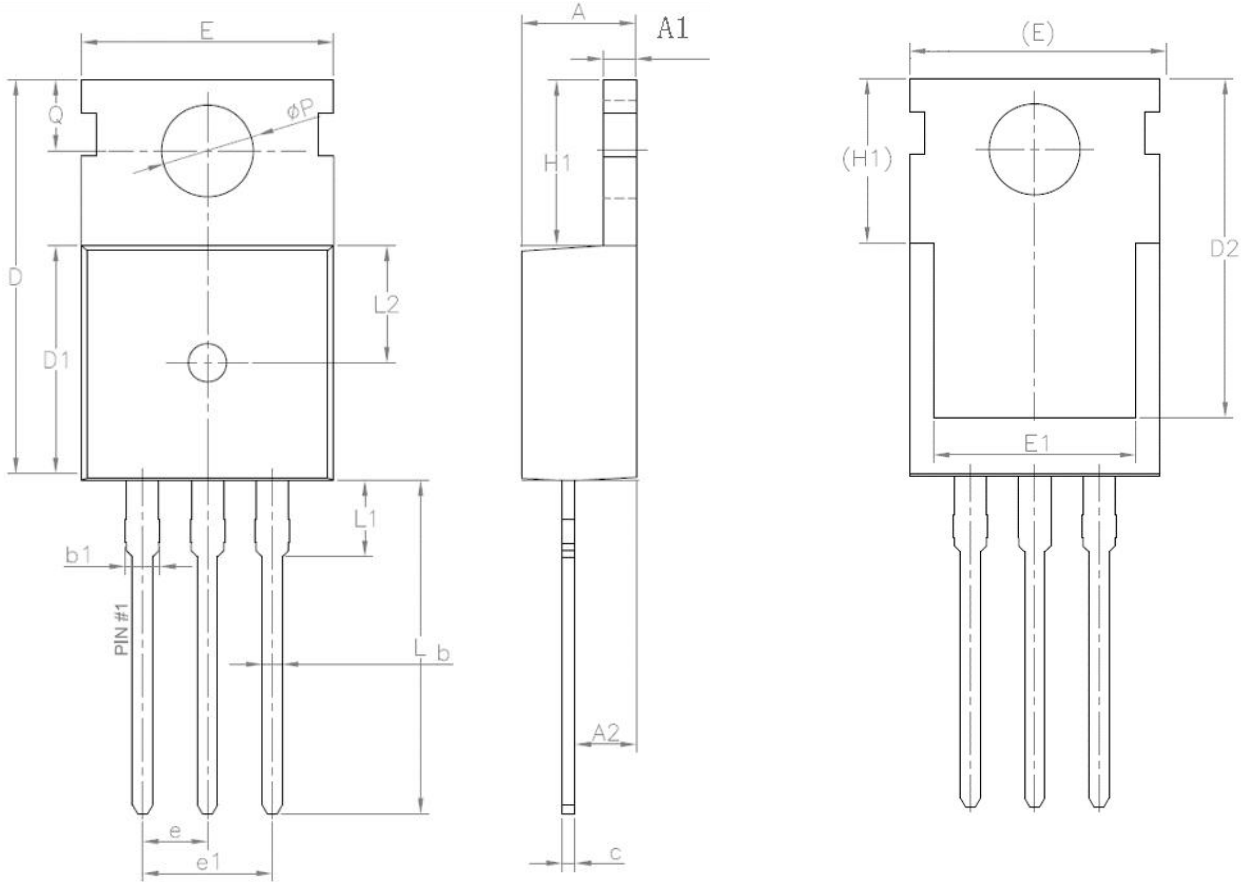
Outlines TO-262 Package



SYMBOL	MIN	NOM	MAX
A	4.40	4.50	4.60
A1	2.20	2.40	2.60
b	0.76	---	0.89
b1	0.75	0.80	0.85
b2	1.23	---	1.37
b3	1.22	1.27	1.32
c	0.47	---	0.60
c1	0.46	0.51	0.56
c2	1.25	1.30	1.35
D	9.10	9.20	9.30

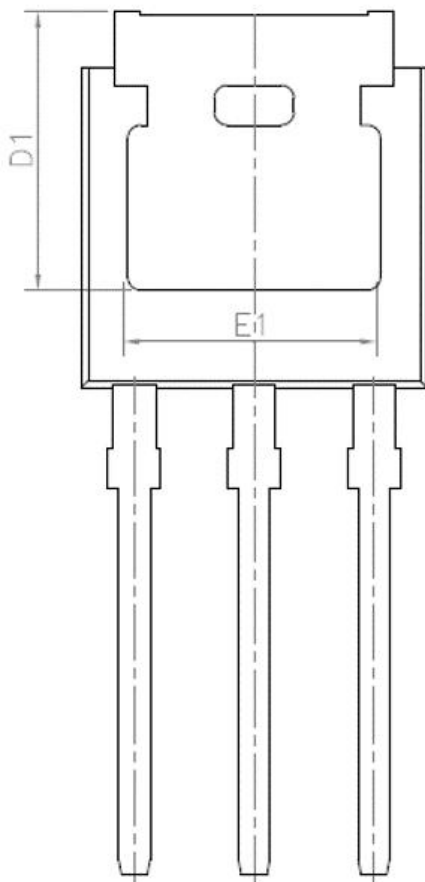
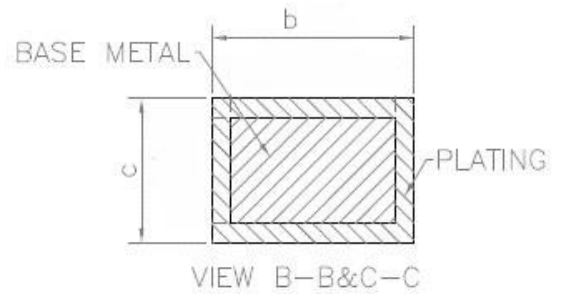
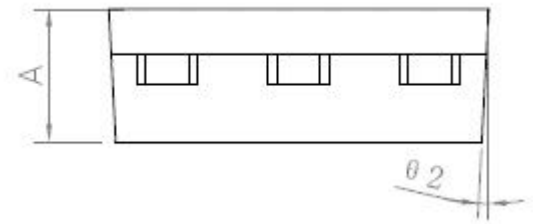
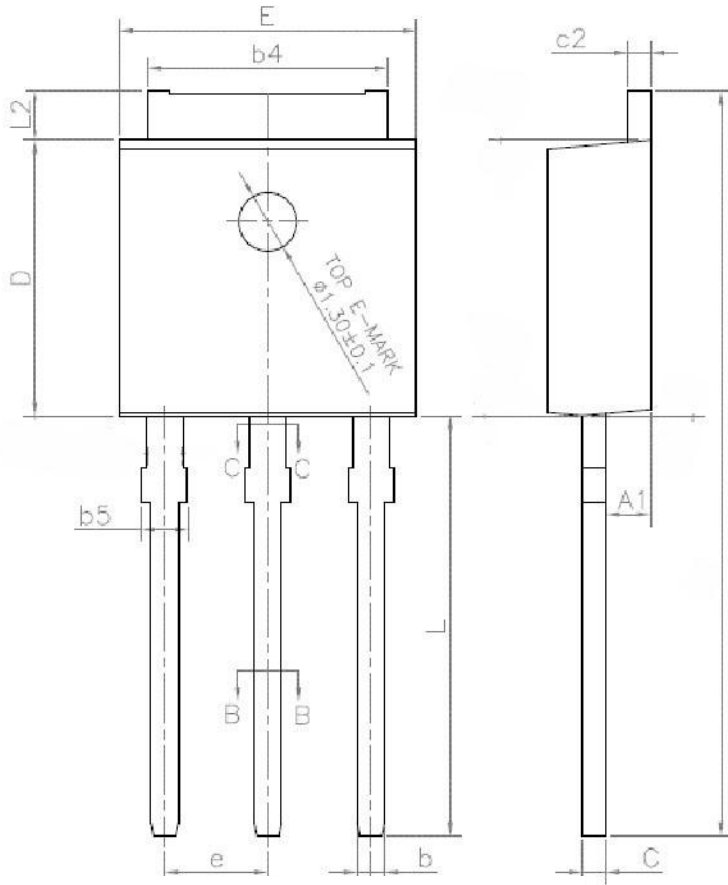
SYMBOL	MIN	NOM	MAX
D1	8.00	---	---
E	9.80	9.90	10.00
E1	7.80	---	---
e	2.54 BSC		
L	12.90	13.20	13.50
L1	2.80	3.00	3.20
L2	1.17	1.27	1.40
L3	4.60 REF		
W	13.25	---	14.00
θ	1°	3°	5°

Outlines TO-220 Package



SYMBOL	MIN	NOM	MAX
A	4.37	4.535	4.7
A1	1.25	1.3	1.4
A2	2.2	2.4	2.6
b	0.7	---	0.95
b1	1.17	---	1.47
c	0.45	0.5	0.6
D	15.1	15.65	16.1
D1	8.8	9.15	9.4
D2	11.8	---	---
E	9.7	9.95	10.3
E1	7	---	---
e	2.54 BSC		
e1	5.08 BSC		
H1	6.25	6.5	6.85
L	12.75	13.29	13.8
L1	---	---	3.5
ϕP	3.4	3.67	3.8
Q	2.6	---	3

Outlines TO-251 Package



SYMBOL	MIN	NOM	MAX
A	2.20	2.30	2.38
A1	0.90	1.04	1.17
b	0.56	--	0.90
b4	5.20	5.33	5.46
b5	--	--	1.05
c	0.43	--	0.61
c2	0.43	--	0.61
D	5.98	6.10	6.22
D1	5.2	--	--
E	6.40	6.60	6.73
E1	4.60	--	--
e	2.24	2.29	2.34
e1	4.47	4.57	4.67
H	16.18	16.50	16.82
L	9	9.35	9.65
L2	0.88	1.05	1.28

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